



10/055270

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PATENT
Attorney's Doc. No. 9898-217

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent No.: US 6,982,205 B2
Inventor: Joo et al.
Issued: January 3, 2006

For: METHOD AND MANUFACTURING A SEMICONDUCTOR DEVICE
HAVING A METAL-INSULATOR-METAL CAPACITOR

Ser. No.: 10/055,270 Filed: January 22, 2002
Group Art Unit: 2814 Examiner: Anh Duy Mai

TRANSMITTAL LETTER

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Certificate

NOV 09 2006

of Correction

Enclosed for filing are the following:

- ☒ Request for Certificate of Correction
- ☒ Certificate of Correction Form PTO 1050 (in duplicate)
- ☒ Return postcard
- ☒ Any deficiency or overpayment should be charged or credited to deposit account number 13-1703.

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.

Scott A. Schaffer
Reg. No. 38,610

MARGER JOHNSON & McCOLLOM, P.C.
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22313-1450

Date: November 3, 2006

Kelly Andrews

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REQUEST FOR CERTIFICATE OF CORRECTION

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P.O. Box 1450
Alexandria, VA 22313-1450

Upon comparison of the above-identified original Letters Patent with applicant's copy of the application therefore, the following error in the original Letters Patent has been noted:

In the cover page, Section 54 please replace "METHOD AND MANUFACTURING A SEMICONDUCTOR DEVICE HAVING A METAL-INSULATOR-METAL CAPACITOR" with -- METHOD FOR MANUFACTURING A SEMICONDUCTOR DEVICE HAVING A METAL-INSULATOR-METAL CAPACITOR--
At column 1, lines 1-4 please replace "METHOD AND MANUFACTURING A SEMICONDUCTOR DEVICE HAVING A METAL-INSULATOR-METAL CAPACITOR" with -- METHOD FOR MANUFACTURING A SEMICONDUCTOR DEVICE HAVING A METAL-INSULATOR-METAL CAPACITOR--
At column 2, line 20 please replace "700° C." with --700° C--
At column 2, line 24 please replace "400° C." with --400° C--
At column 5, line 14 please replace "(C₅H₅(" with --(C₅H₅)(--
At column 5, line 25 please replace "C.," with --C,--
At column 5, line 32 please replace "C." with --C--
At column 5, line 50 please replace "C.," with --C,--
At column 5, line 53 please replace "C.," with --C,--
At column 5, line 66 please replace "C." with --C--
At column 7, line 20 please replace "C.," with --C,--
At column 7, line 43 please replace "C.," with --C,--
At column 9, line 37 please replace "of tantalum" with --of a tantalum--
At column 9, line 39 please replace "dielectric occurs" with --dielectric layer occurs--
At column 10, line 4 please replace "electrode subjecting" with --electrode; subjecting--

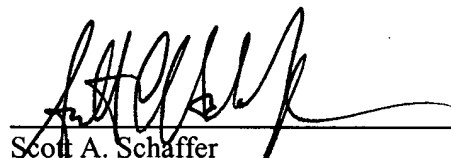
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At column 10, line 7 please replace "of tantalum" with --of a tantalum--
At column 10, line 9 please replace "dielectric" with --dielectric layer--
At column 10, line 30 please replace "under a plasma" with --under plasma--
At column 10, line 31 please replace "oxide (Ta₂O₅) capacitor dielectric layer"
with --oxide layer--
At column 10, line 35 please replace "of tantalum" with --of a tantalum--
At column 10, line 37 please replace "occurs;" with --occurs; and--
At column 10, line 42 please replace "C.," with --C,--

Applicant respectfully requests that a Certificate of Correction calling attention to the above error be issued pursuant to Rule 322 of the Patent Office and Title 35, United States Code, Section 254. Two copies of a Certificate of Correction form are enclosed.

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.



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38,610

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Kelly Andrews

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PATENT NO : US 6,982,205 B2

DATED : January 3, 2006

INVENTOR(S) : Joo et al.

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At column 5, line 66 please replace "C." with --C--

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MAILING ADDRESS OF SENDER:

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